



Monte Carlo simulations as a tool for the development of a new reference ionisation chamber

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<http://www.irmm.jrc.be>
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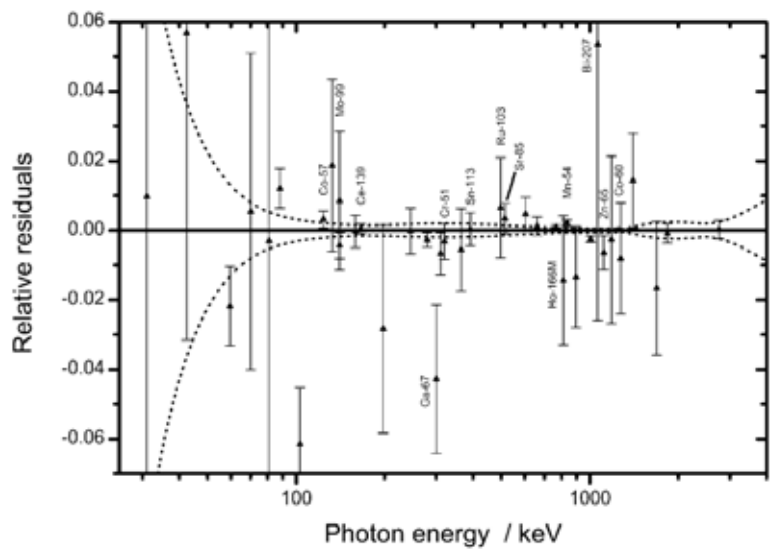
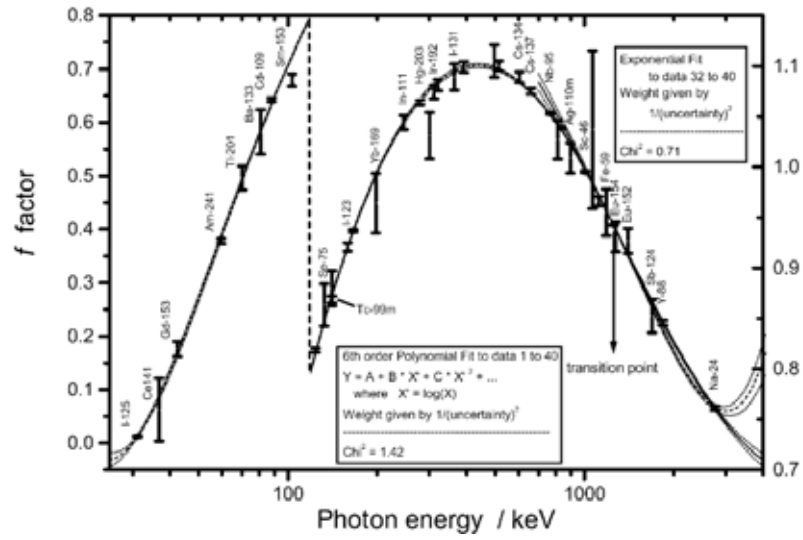


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Motivation



SIR (Système International de Référence) chamber at BIPM

- 4π well-type ionisation chamber (IG11, 2 MPa N₂)
- 30 years of calibrations, >60 radionuclides (photon and pure beta)
- Comparison with ²²⁶Ra reference source (equivalent activity A_e)

BUT

- What if any component breaks down?
- Sensitivity to low photon energies

C. Michotte, Appl. Rad. Isot. 56 (2002)15-20





Motivation

Development of a new reference IC:

“determination of design and operation criteria for a cylindrical IC system which should guarantee a reproducible output at the level of a few tenths of a percent for different chambers constructed according to these criteria”

- Original idea : Reher (IRMM), Woods (NPL), Denecke (IRMM)
- Proto-type chamber based on NPL IC
- MC simulations :
 - L. Johansson, A. Švec/J. Gasparro (EGS-4),
 - this work (MCNP)

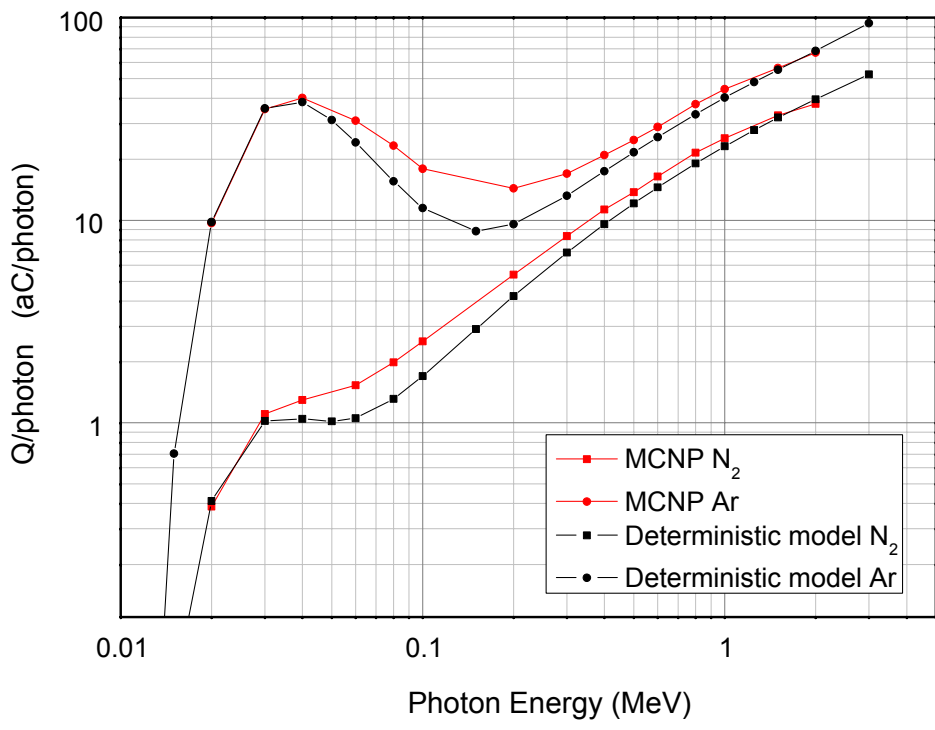
.. MC simulations

In development process several methods used :

- Deterministic model of cylindrical IC
- Measurements with proto-type chamber
- MC simulations

MCNP4c

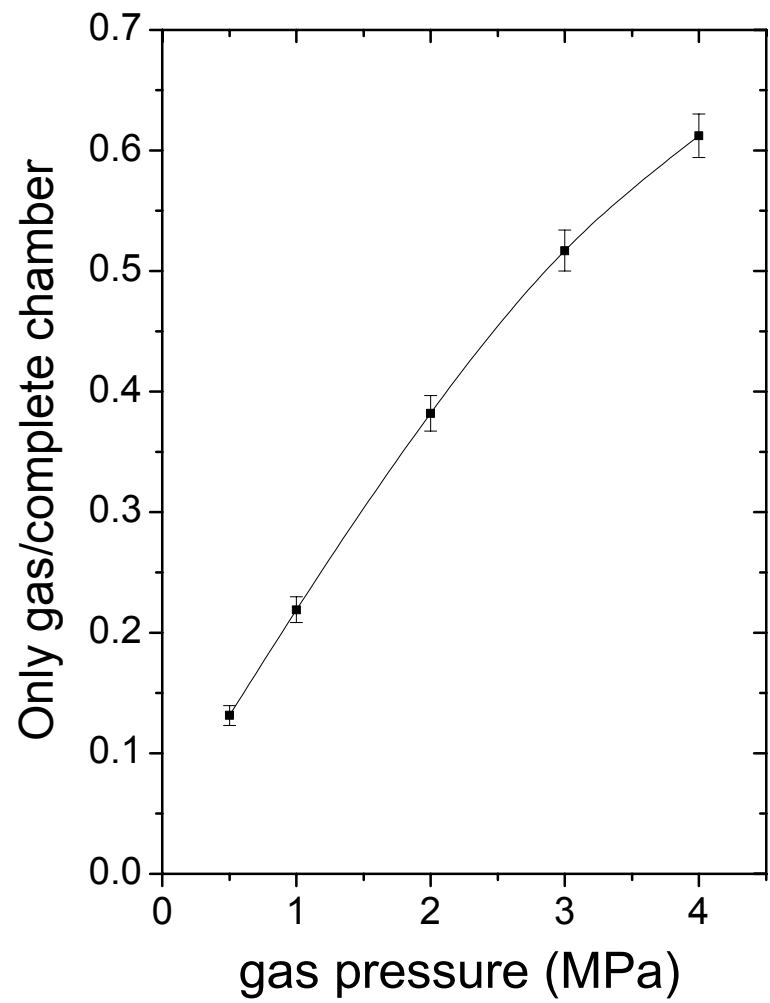
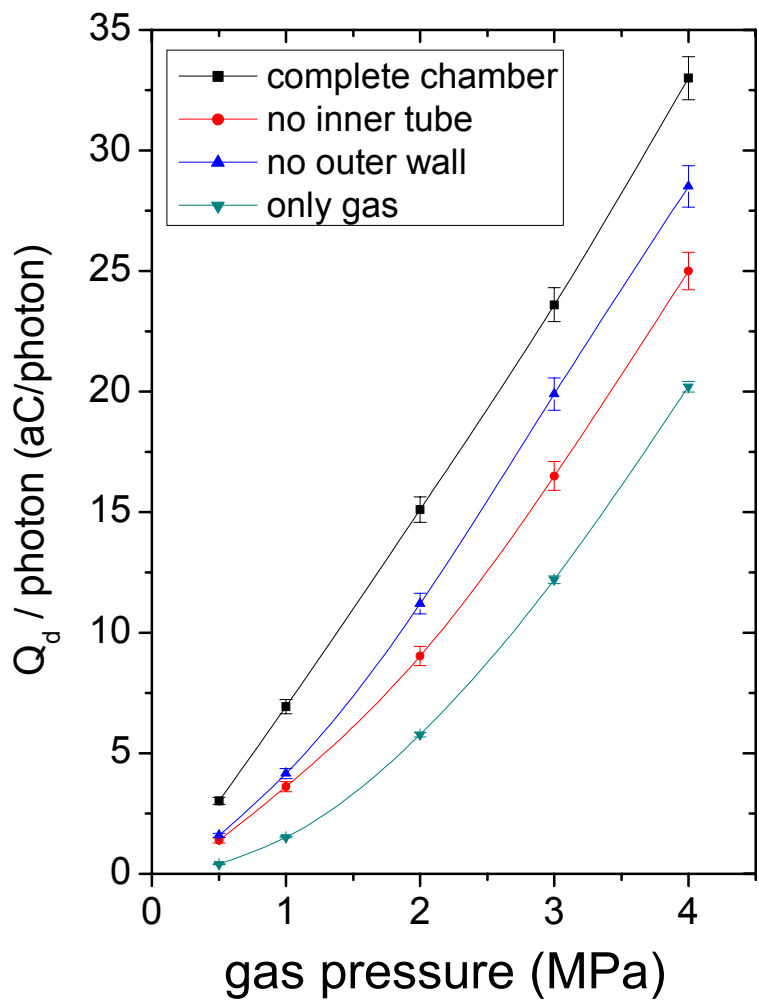
MCNP5.1



.. MC simulations

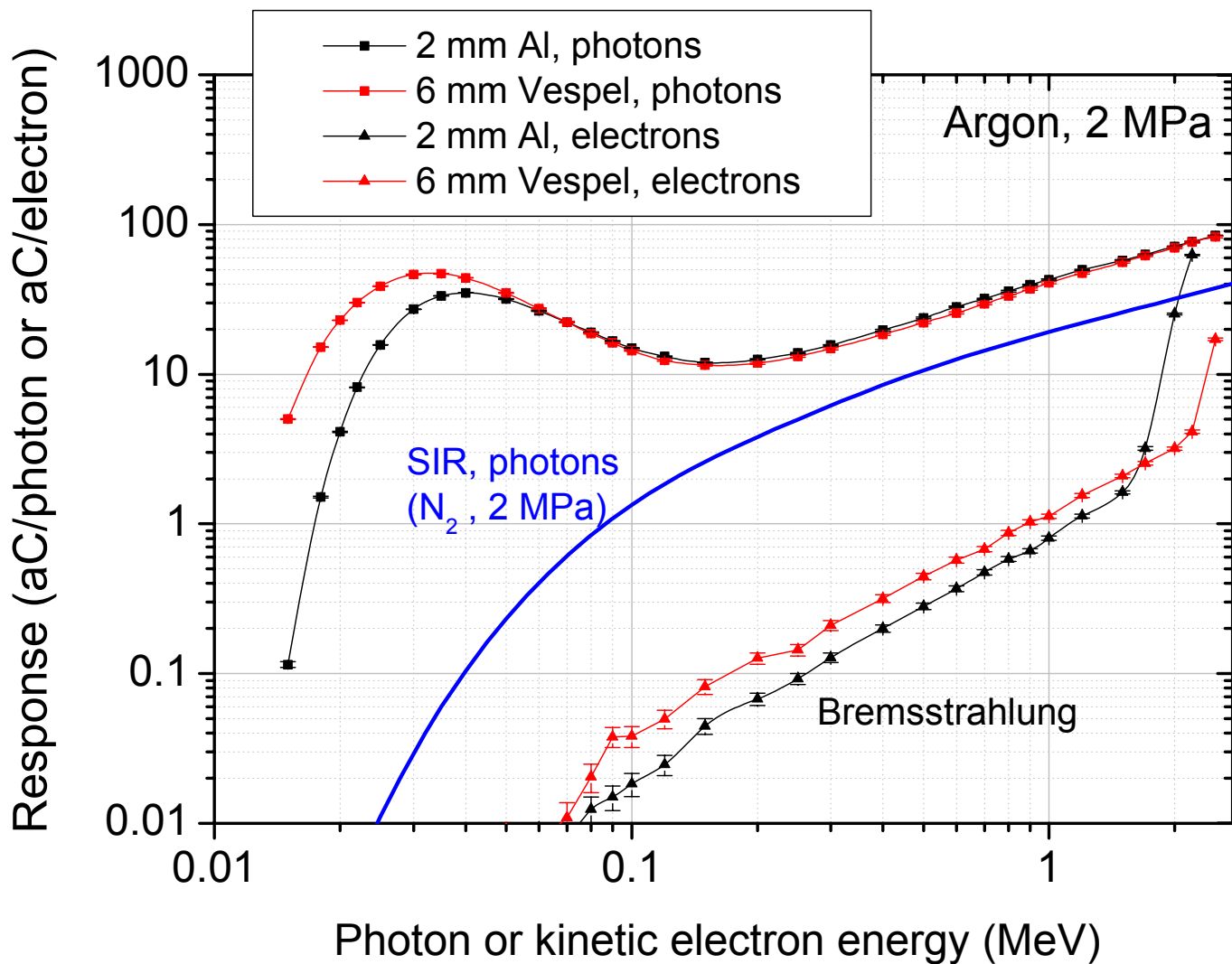
Several contributions to ionisation current

Argon, MCNP, 1 MeV photons



.. MC simulations

Start from proto-type IC: photon and electron response (MCNP)



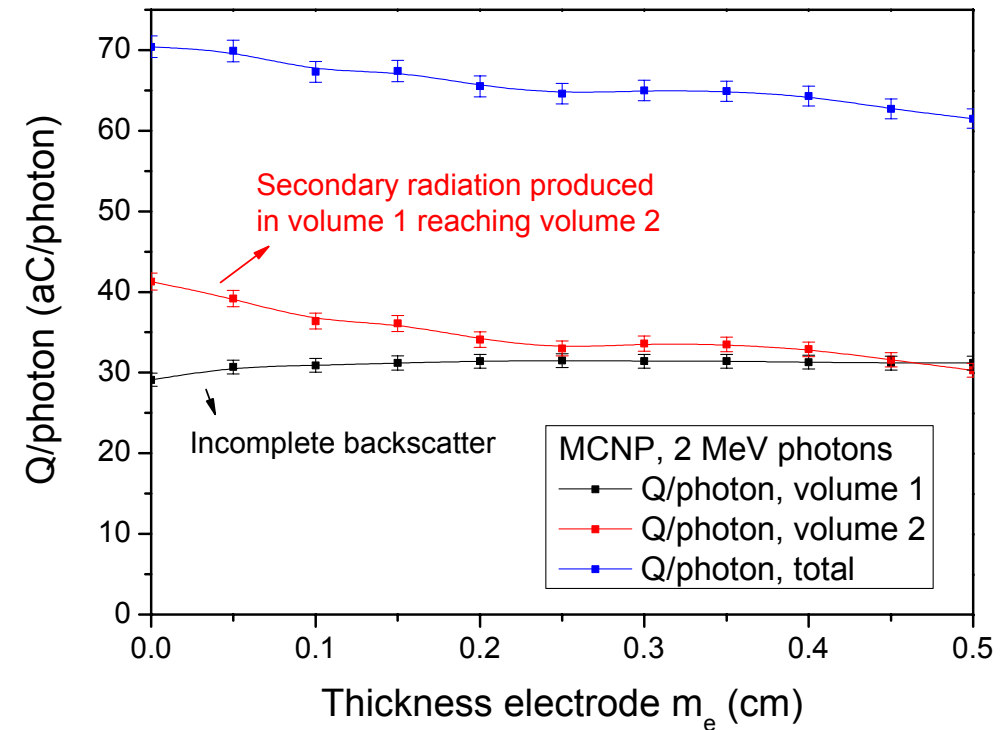
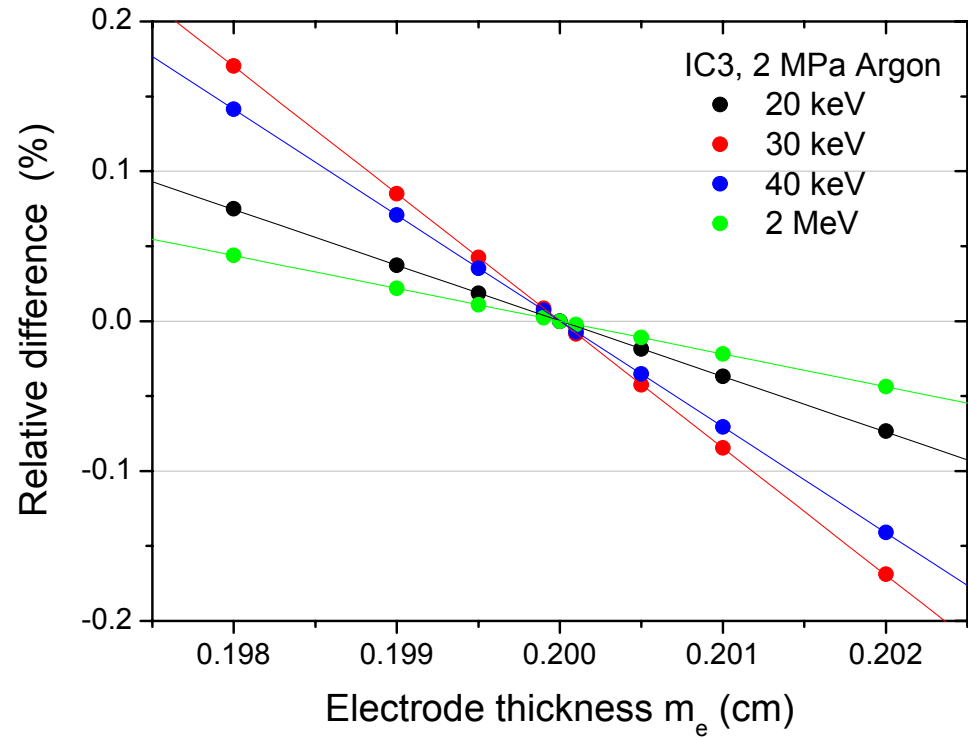
Vespel
 $C_{22}H_{10}O_5N_2$



.. MC simulations

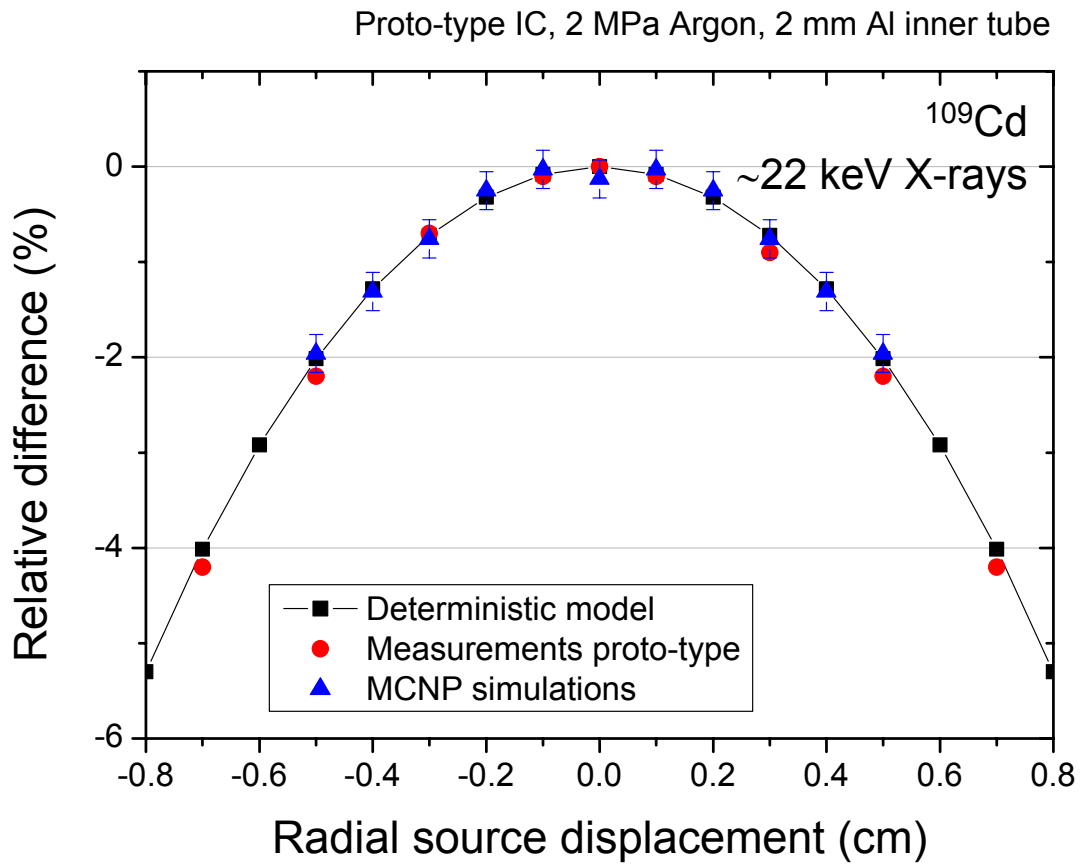
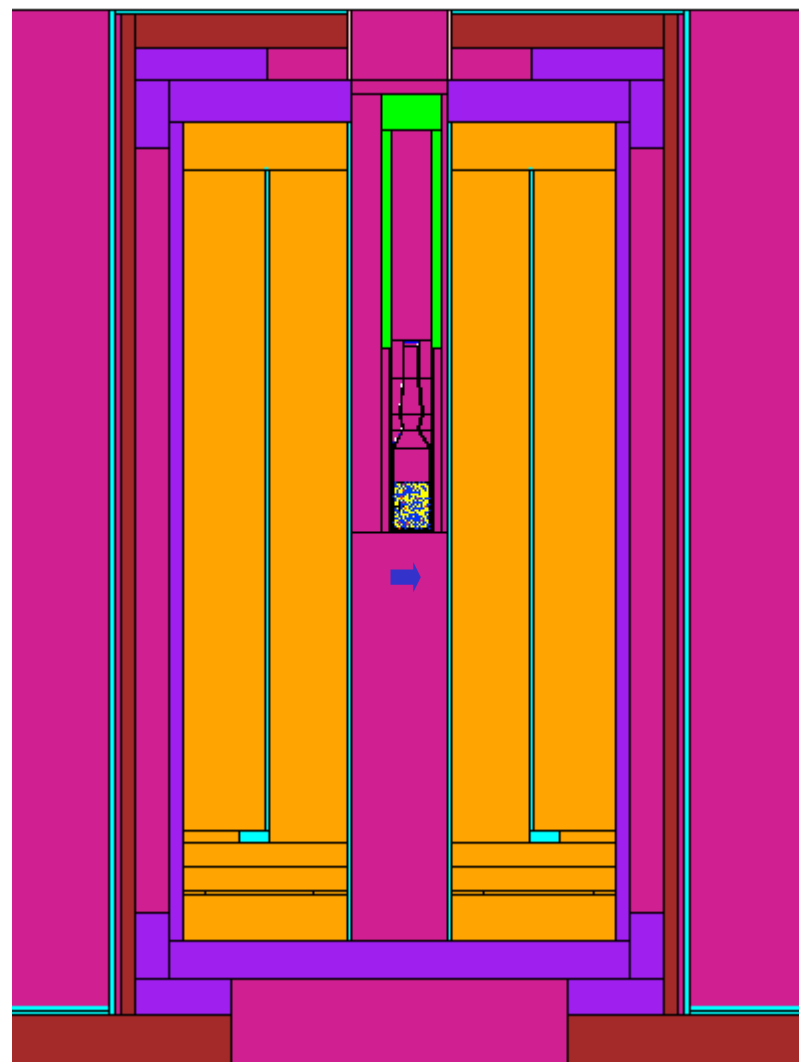
Determination of tolerances on IC system parameters for a 0.1% variation in output (20 keV to 2 MeV)

Example 1. IC response as a function of electrode thickness



.. MC simulations

Example 2. Determination of effect of radial source displacements

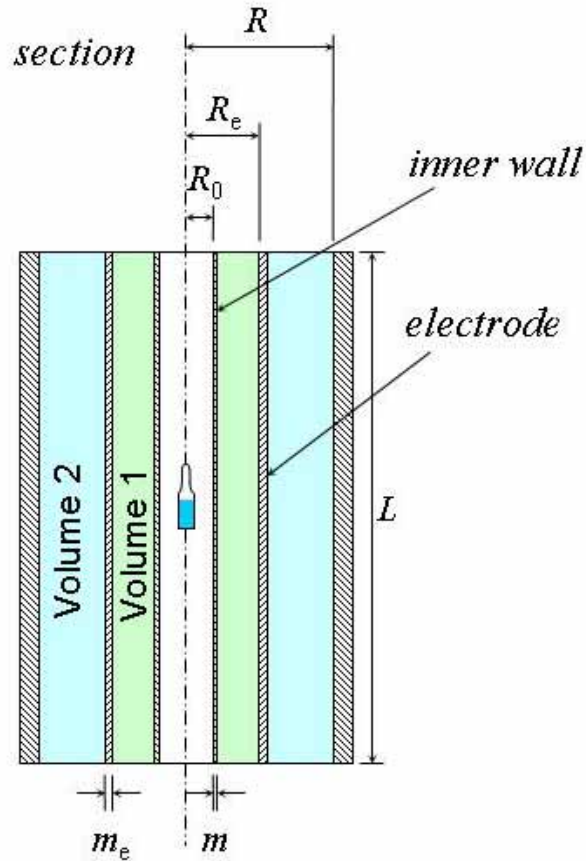


→ tolerance for 0.1% : 0.9 mm for optimised design



.. MC simulations

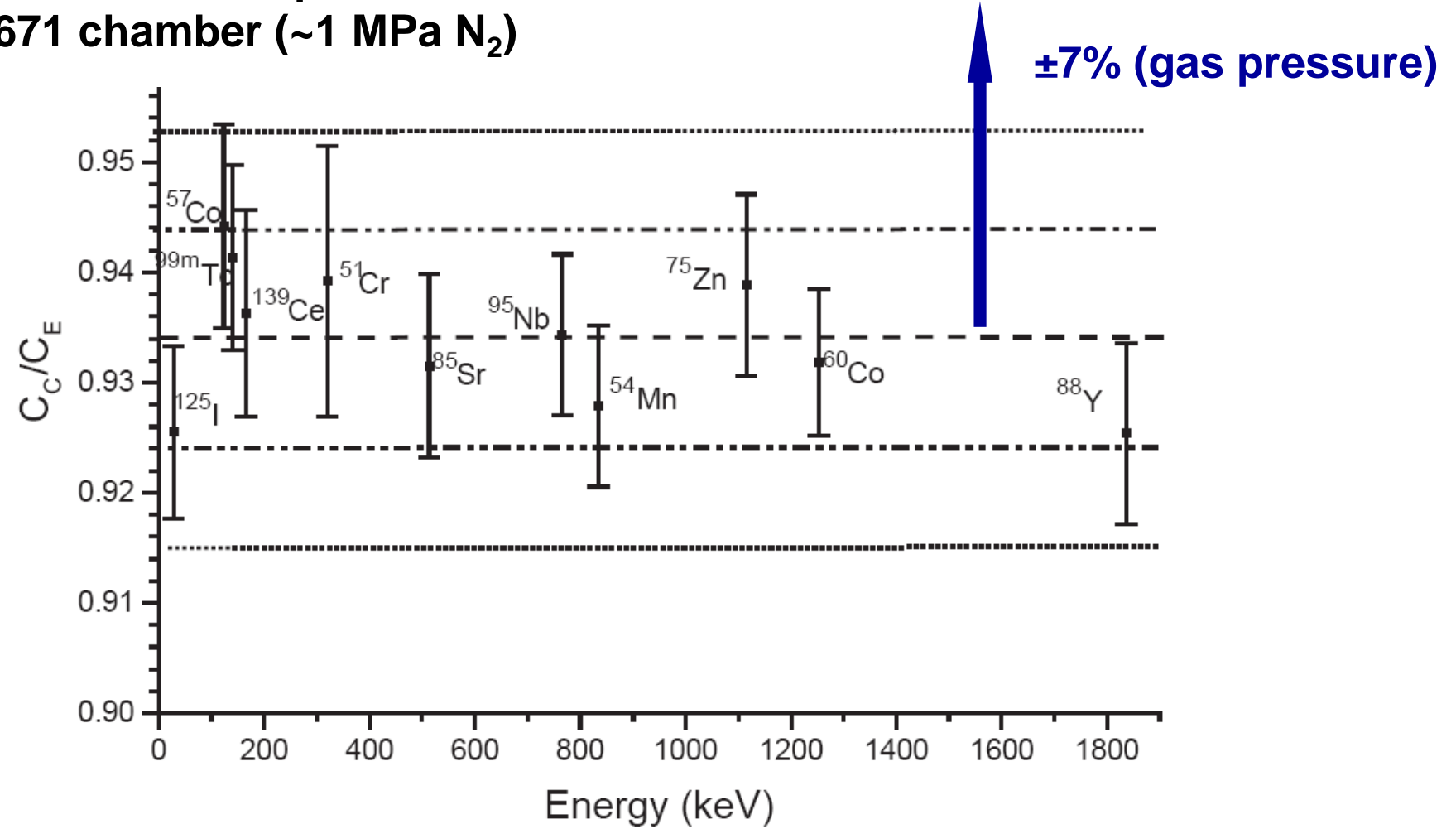
New reference chamber ...



Item	Value/statement	Required tolerance
L	35-40 cm	1.6 mm (2 MeV)
R	9 - 9.5 cm	70 μm (2 MeV)
R_0	2.5 – 3 cm	55 μm (30 keV)
R_e	5.5 cm	60 μm (20 keV)
Inner wall	Aluminium/Vespel	
m (thickness inner wall)	0.2 cm Al / 0.6 cm Vespel	1 μm /15 μm (20 keV)
Electrode	Aluminium	
m_e (thickness electrode)	0.3 cm	14 μm (30 keV)
Filling gas	Argon	
Gas pressure	2 MPa	2 kPa (2 MeV)
Source positioning	center	0.9 mm (20 keV, Al)

.... Towards absolute MC ..

PENELOPE MC / Experiment
Vinten 671 chamber (~1 MPa N₂)



A. De Vismes, M.N. Amiot, Appl. Rad. Isot. 59 (2003) 267-272

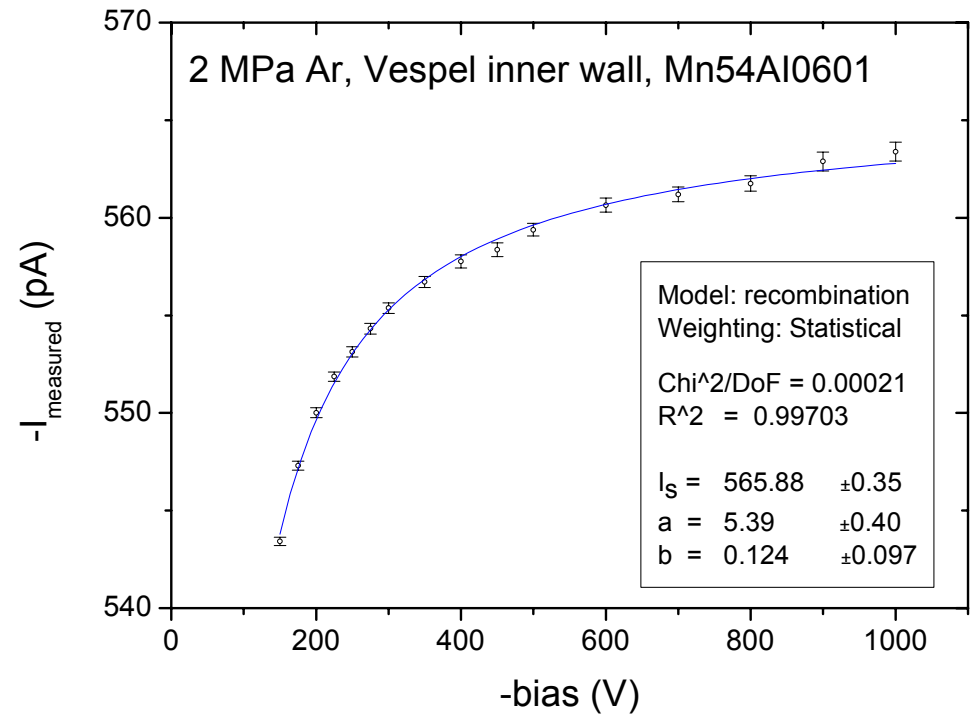


Joint Research Centre

.... Towards absolute MC ..

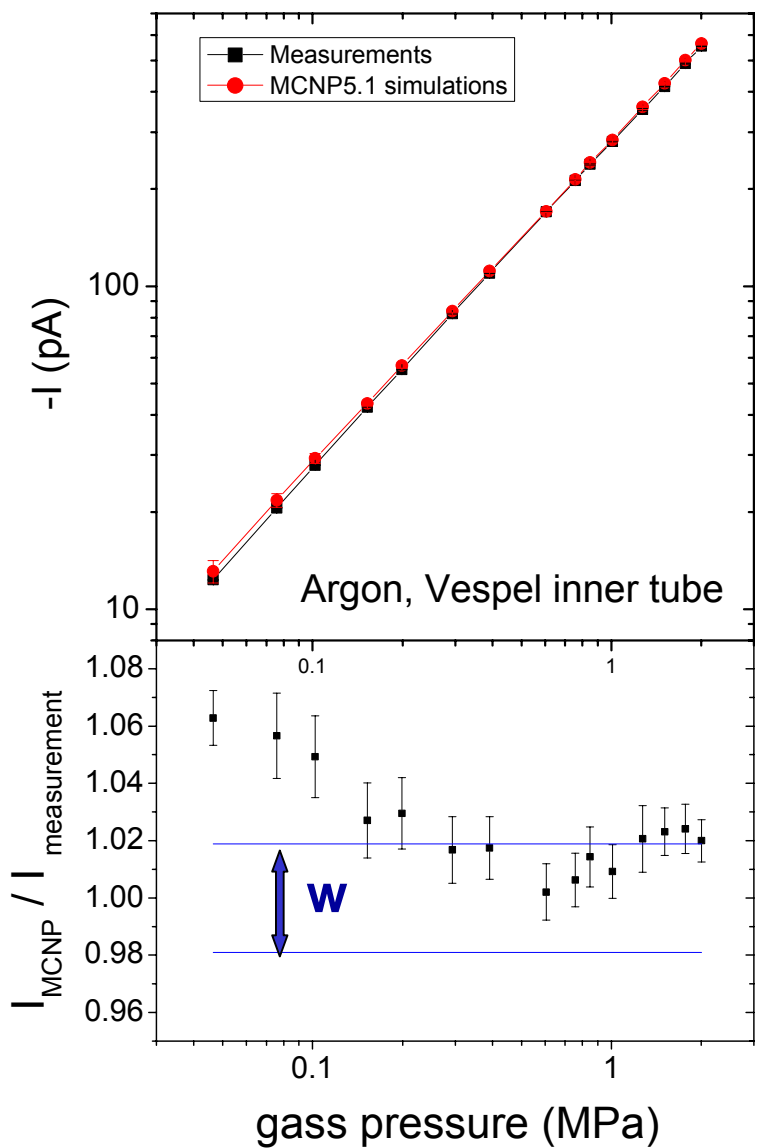
Can we get absolute agreement between MC and measurements ?

- Proto-type IC : Geometrical parameters well-known
- Pressure controlled with traceable RUSKA pressure balance
- Measurement of ^{54}Mn source (834.8 keV) as function of gas pressure
- Ion loss (recombination, diffusion)?
 - determination of saturation current (I_s)



$$\frac{I}{I_s} = 1 - \frac{a}{U} - \frac{b}{U^2} I$$

.... Towards absolute MC ..



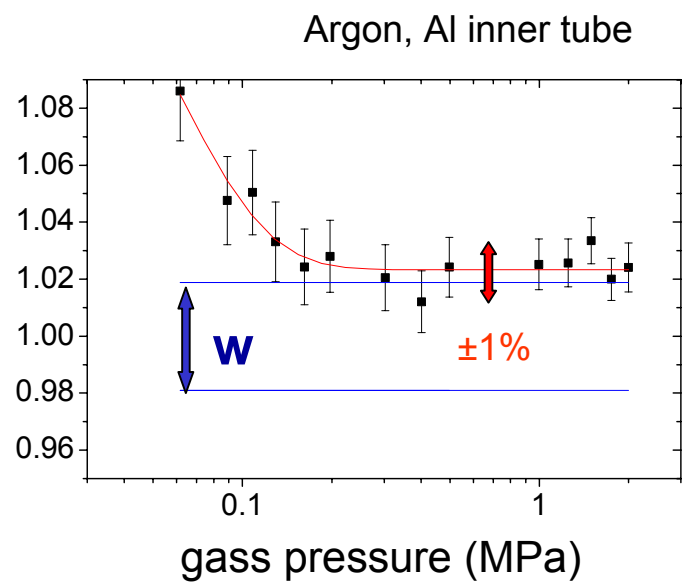
Measurements :

absolute measurement of current ($\delta I/I > 1\%$)

Simulations :

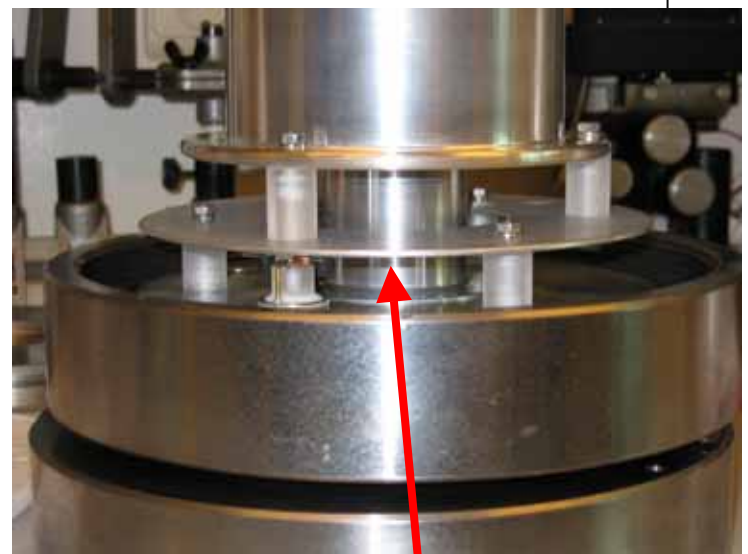
MCNP, *F8 tally : E_d (MeV/particle)

$$Q_d = \frac{e E_d}{W} \quad W_{Ar} = 26.4 \text{ eV} \pm 0.5 \text{ eV} \quad (\text{ICRU31})$$

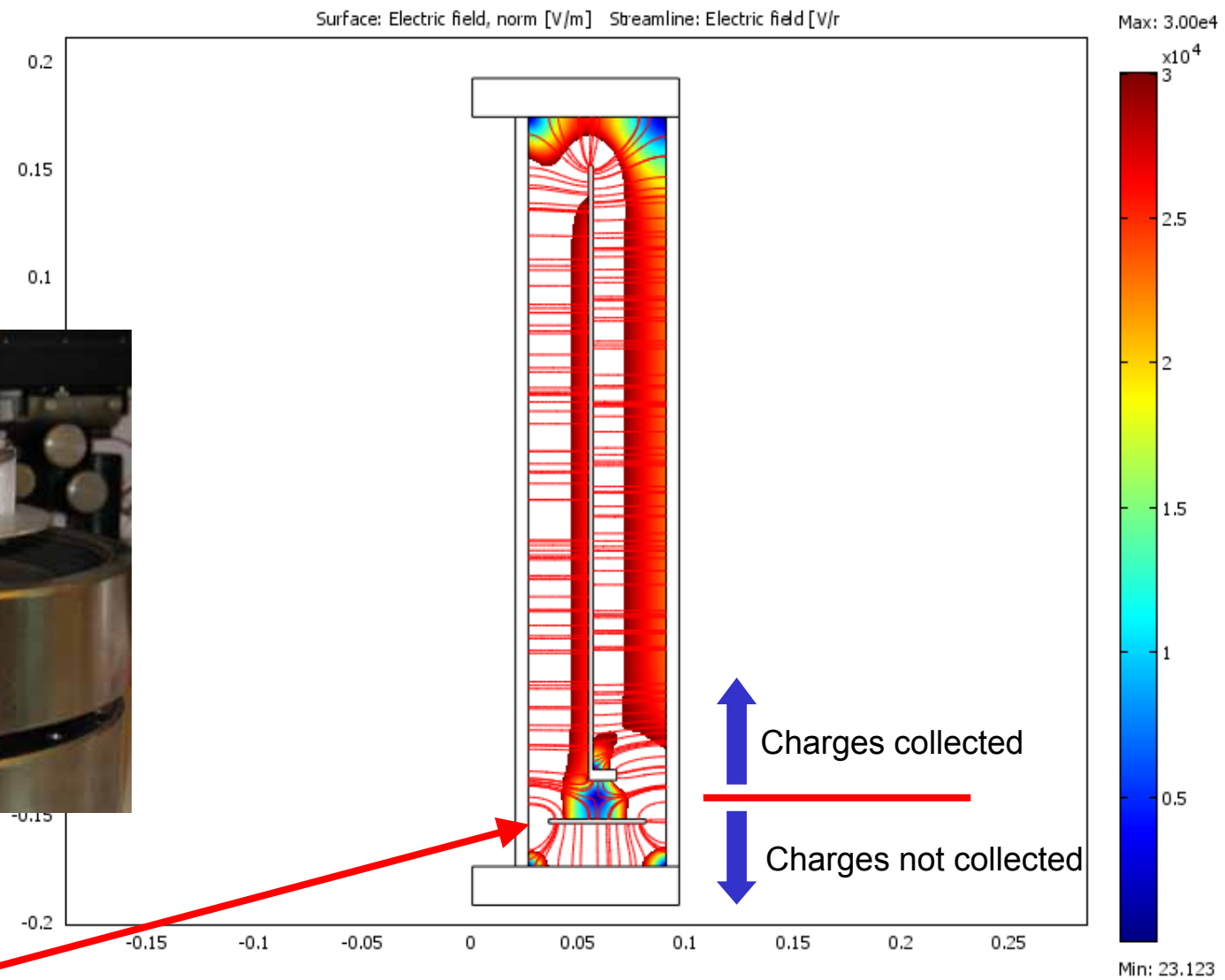


.... Towards absolute MC ..

Definition of volume



Guard ring





.....Conclusions

- **Tolerances on geometrical and operational parameters for a new reference IC system were determined with MC simulations (MCNP)**
- **Absolute agreement between measurements and MC simulations (limited by uncertainty on W-value!)**
- **New reference chamber will be built and tested in near future**